

Amendments to the Specification:

Please replace the paragraphs on pages 33-34 under Example 1, with the following amended paragraphs:

A ~~first~~ HTL is first deposited onto the ITO (indium tin oxide) coated glass substrate. The ~~first~~ HTL consists of 400 Å of R854. A ~~second HTL~~ first electron transporting layer, which is also a blocking layer, consisting of TAZ, having a thickness of about 20 nm (200 Å) is deposited onto the HTL layer. The first electron transporting layer is doped with Ir(ppy)₃. A second electron transport layer of Alq₃ having a thickness of about 20 nm is deposited onto the first electron transporting layer. The device is finished by depositing a Mg--Ag electrode onto the second electron transporting layer. This Mg--Ag electrode has of thickness 100 nm. All of the depositions are carried out at a vacuum less than 5×10^{-5} Torr. The devices are tested in air, without packaging.

When a voltage is applied between the cathode and the anode, holes are injected from ITO to NPD and transported by the NPD layer, while electrons are injected from MgAg to Alq₃ and transported through Alq₃. Then holes and electrons are injected into the first electron transporting layer ~~and~~ where carrier recombination occurs ~~in BCP~~, the excited states were formed, and the dopant molecules are excited and decay radiatively.